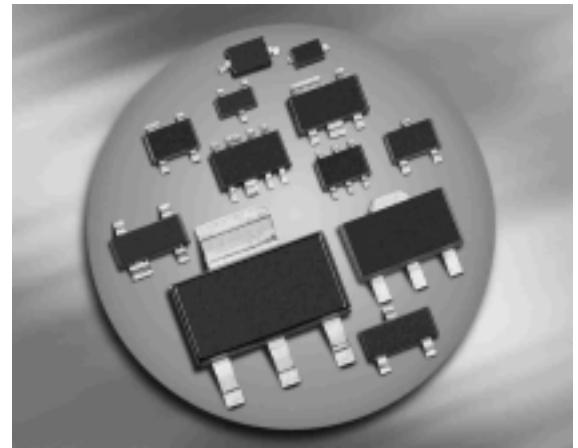
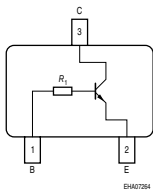


NPN Silicon Digital Transistor

- Switching circuit, inverter, interface circuit, driver circuit
- Built in bias resistor ($R_1 = 47 \text{ k}\Omega$)


BCR149F/L3
BCR149T


Type	Marking	Pin Configuration						Package
BCR149F*	UAs	1=B	2=E	3=C	-	-	-	TSFP-3
BCR149L3*	UA	1=B	2=E	3=C	-	-	-	TSFP-3-4
BCR149T*	UA	1=B	2=E	3=C	-	-	-	SC75

* Preliminary

Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-emitter voltage	V_{CEO}	50	V
Collector-base voltage	V_{CBO}	50	
Input forward voltage	$V_{i(fwd)}$	80	
Input reverse voltage	$V_{i(rev)}$	5	
Collector current	I_C	70	mA
Total power dissipation- BCR149F, $T_S \leq 128^\circ\text{C}$ BCR149L3, $T_S \leq 135^\circ\text{C}$ BCR149T, $T_S \leq 109^\circ\text{C}$	P_{tot}	250 250 250	mW
Junction temperature	T_j	150	
Storage temperature	T_{stg}	-65 ... 150	

Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point ¹⁾	R_{thJS}		K/W
BCR149F		≤ 90	
BCR149L3		≤ 60	
BCR149T		≤ 165	

Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	

DC Characteristics

Collector-emitter breakdown voltage $I_C = 100 \mu\text{A}$, $I_B = 0$	$V_{(BR)CEO}$	50	-	-	V
Collector-base breakdown voltage $I_C = 10 \mu\text{A}$, $I_E = 0$	$V_{(BR)CBO}$	50	-	-	
Collector-base cutoff current $V_{CB} = 40 \text{ V}$, $I_E = 0$	I_{CBO}	-	-	100	nA
Emitter-base cutoff current $V_{EB} = 5 \text{ V}$, $I_C = 0$	I_{EBO}	-	-	100	nA
DC current gain ²⁾ $I_C = 5 \text{ mA}$, $V_{CE} = 5 \text{ V}$	h_{FE}	120	-	630	-
Collector-emitter saturation voltage ²⁾ $I_C = 10 \text{ mA}$, $I_B = 0.5 \text{ mA}$	V_{CEsat}	-	-	0.3	V
Input off voltage $I_C = 100 \mu\text{A}$, $V_{CE} = 5 \text{ V}$	$V_{i(off)}$	0.4	-	0.8	
Input on voltage $I_C = 2 \text{ mA}$, $V_{CE} = 0.3 \text{ V}$	$V_{i(on)}$	0.5	-	1.5	
Input resistor	R_1	32	47	62	k Ω

AC Characteristics

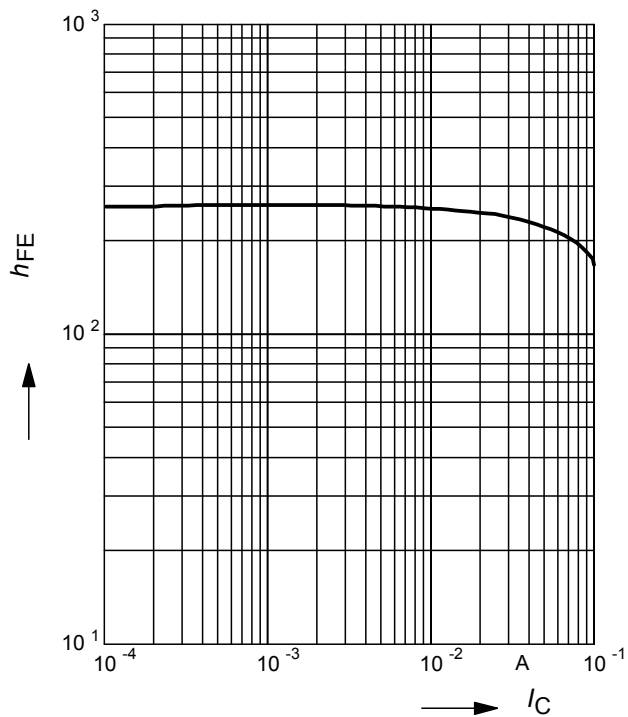
Transition frequency $I_C = 10 \text{ mA}$, $V_{CE} = 5 \text{ V}$, $f = 100 \text{ MHz}$	f_T	-	150	-	MHz
Collector-base capacitance $V_{CB} = 10 \text{ V}$, $f = 1 \text{ MHz}$	C_{cb}	-	3	-	pF

¹⁾For calculation of R_{thJA} please refer to Application Note Thermal Resistance

²⁾Pulse test: $t < 300 \mu\text{s}$; $D < 2\%$

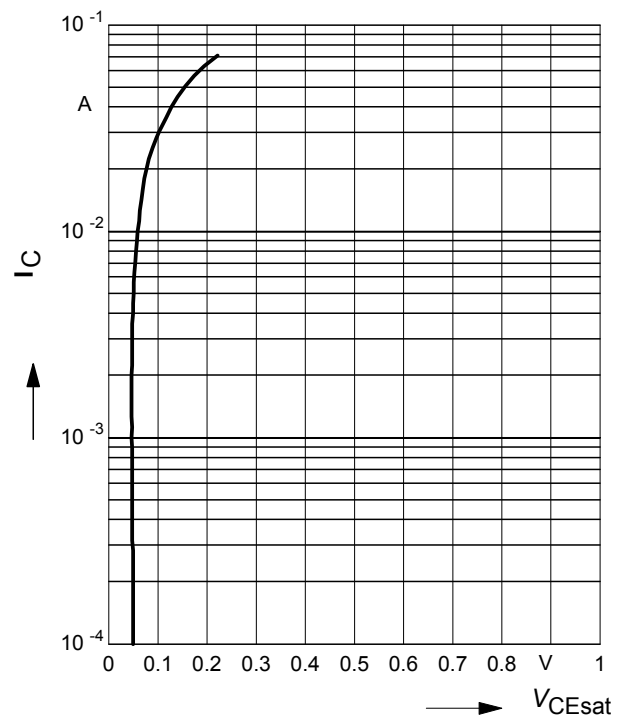
DC current gain $h_{FE} = f(I_C)$

$V_{CE} = 5 \text{ V}$ (common emitter configuration)



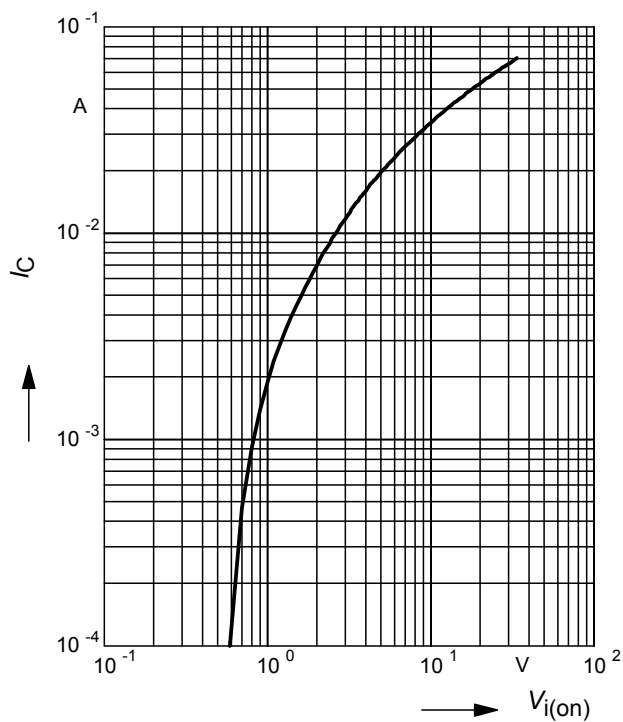
Collector-emitter saturation voltage

$V_{CEsat} = f(I_C)$, $h_{FE} = 20$



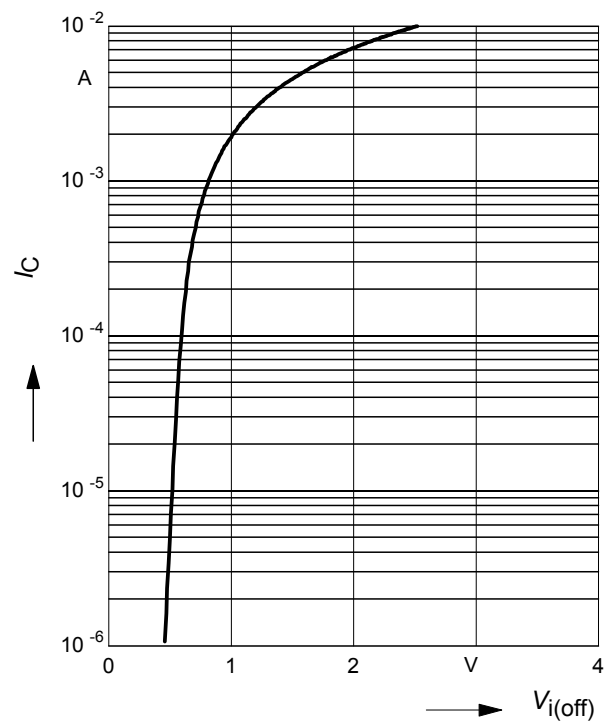
Input on Voltage $V_{i(on)} = f(I_C)$

$V_{CE} = 0.3 \text{ V}$ (common emitter configuration)



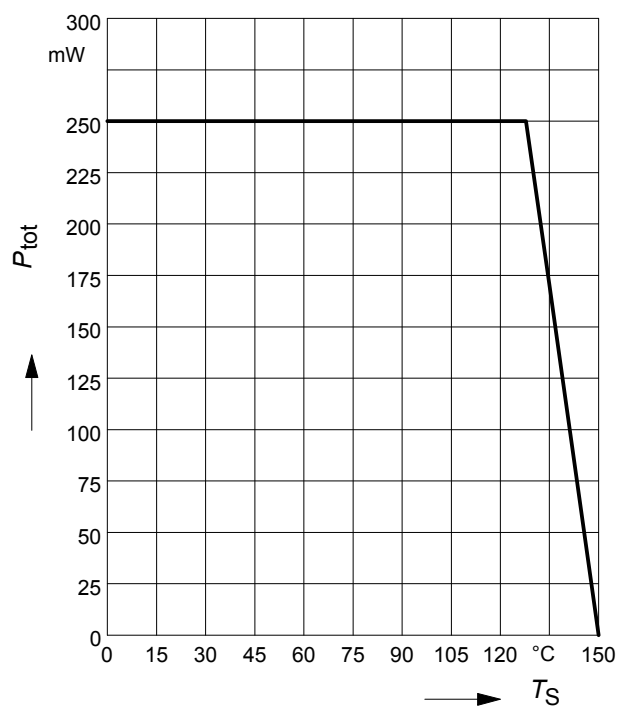
Input off voltage $V_{i(off)} = f(I_C)$

$V_{CE} = 5 \text{ V}$ (common emitter configuration)



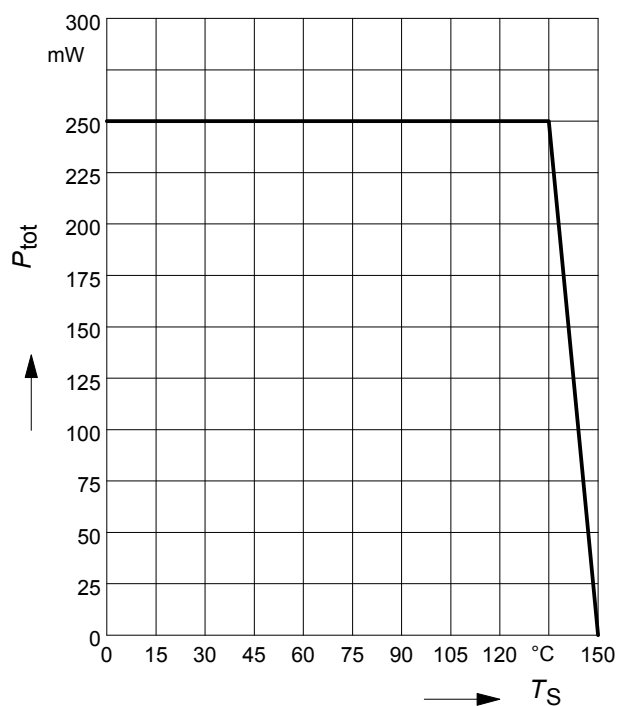
Total power dissipation $P_{\text{tot}} = f(T_S)$

BCR149F



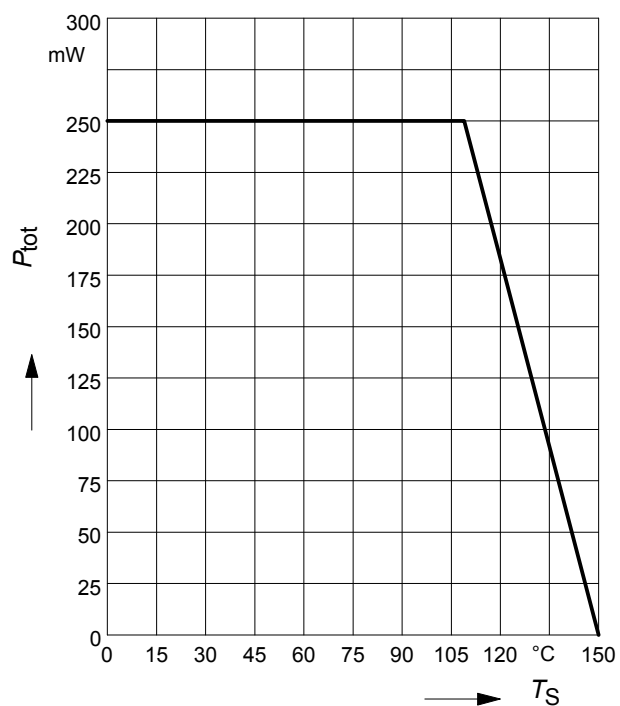
Total power dissipation $P_{\text{tot}} = f(T_S)$

BCR149L3



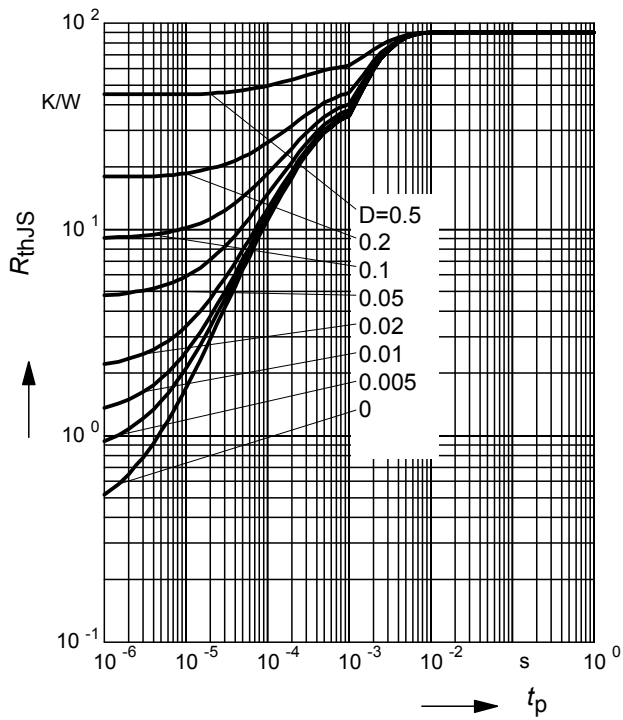
Total power dissipation $P_{\text{tot}} = f(T_S)$

BCR149T



Permissible Puls Load $R_{thJS} = f(t_p)$

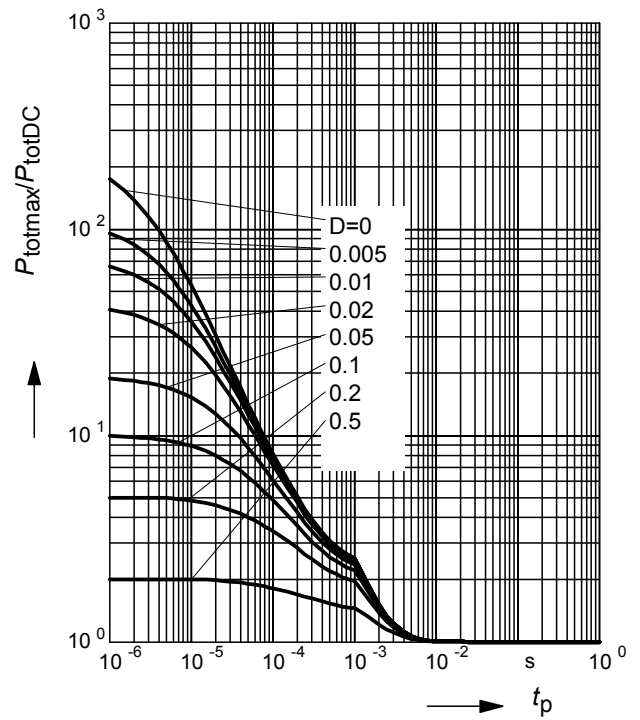
BCR149F



Permissible Pulse Load

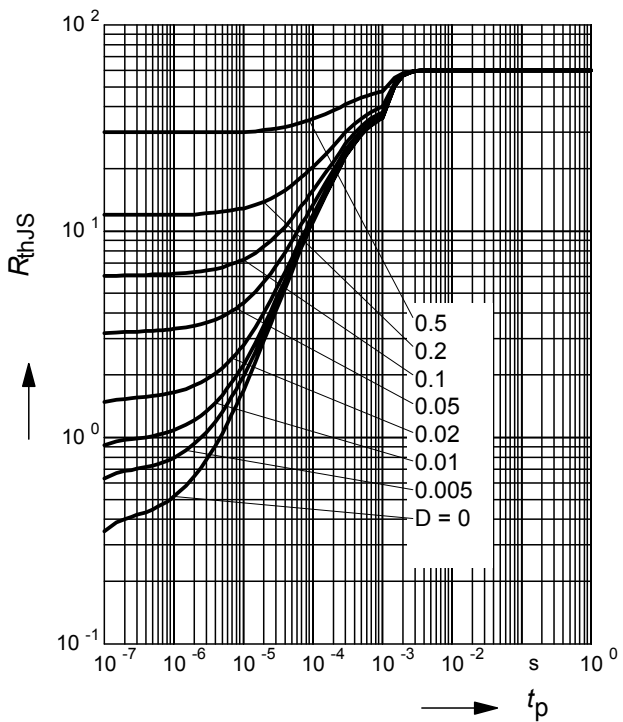
$$P_{totmax}/P_{totDC} = f(t_p)$$

BCR149F



Permissible Puls Load $R_{thJS} = f(t_p)$

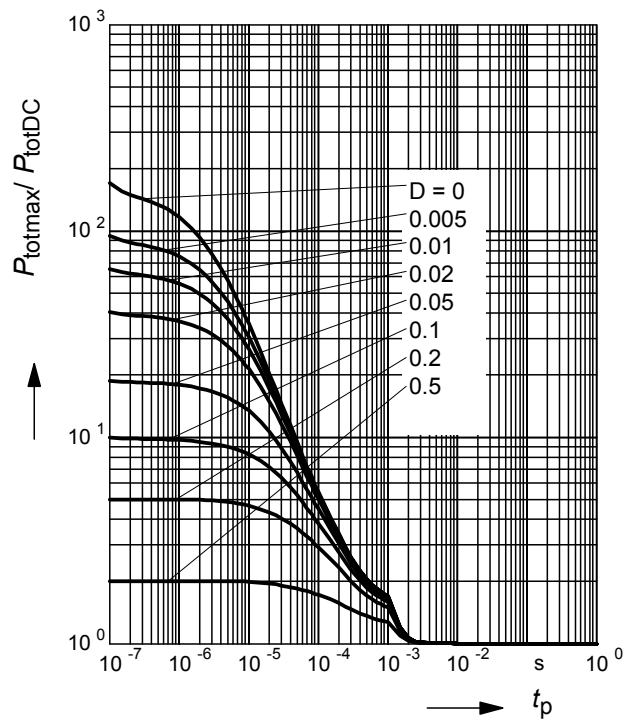
BCR149L3



Permissible Pulse Load

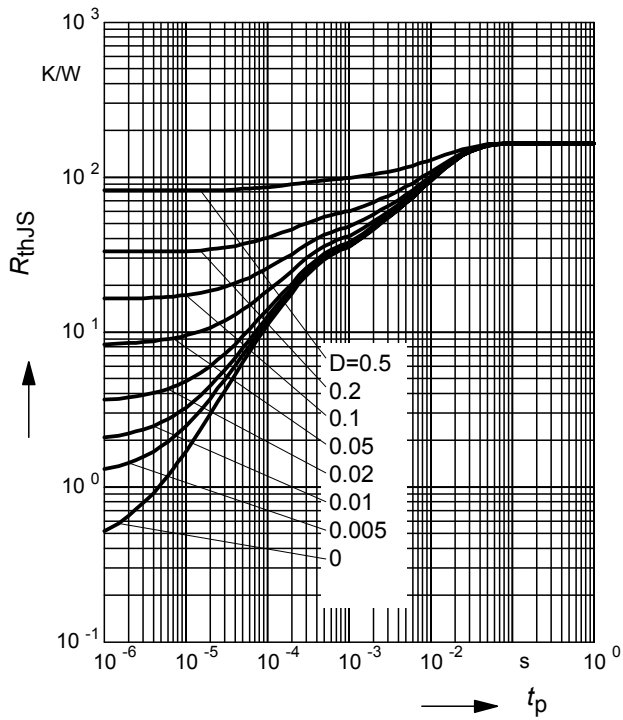
$$P_{totmax}/P_{totDC} = f(t_p)$$

BCR149L3



Permissible Puls Load $R_{thJS} = f(t_p)$

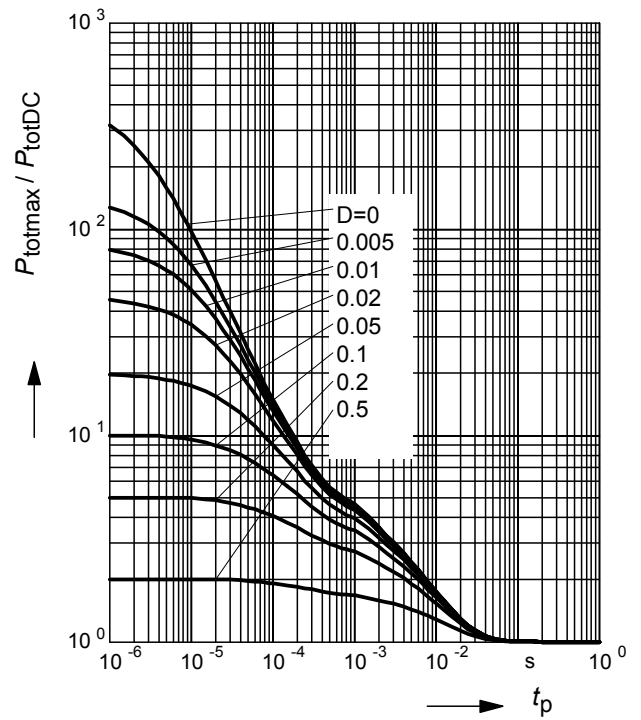
BCR149T



Permissible Pulse Load

$$P_{totmax}/P_{totDC} = f(t_p)$$

BCR149T



The technical drawing shows two views of the M8000-1000 cable gland:

- Front View (Left):** Shows the main body with a total width of 1.6 ± 0.2 . The distance between the mounting holes is $0.2^{+0.1}_{-0.05}$. The height of the main body is $0.2^{+0.1}_{-0.05}$. The mounting hole diameter is $\varnothing 0.10$ (M). The distance from the bottom edge to the center of the mounting hole is 0.5 .
- Side View (Right):** Shows the profile of the gland. The maximum height is 1.9 ± 0.2 . The maximum width of the flange is 0.7 ± 0.1 . The maximum thickness of the flange is 0.1 MAX. . The angle of the flange is 10° MAX. . The distance from the top edge to the start of the flange is 0.15 ± 0.1 . The distance from the bottom edge to the start of the flange is 0.8 ± 0.1 .

Technical drawing of a mechanical part with dimensions:

- Overall width: 1.15
- Overall height: 0.65
- Top flange width: 0.4
- Top flange height: 0.65
- Bottom flange width: 0.4
- Bottom flange height: 0.65
- Central hole diameter: 0.5
- Distance from center to outer edge: 0.5

Diagram illustrating the label structure for the WHN label:

- 2005, December**
Date code
- WHN**
- BCR108T**
Type code
- Pin 1**

Date Code marking for discrete packages with one digit (SCD80, SC79, SC75¹⁾) CES-Code

Month	2003	2004	2005	2006	2007	2008	2009	2010	2011	2012	2013	2014
01	a	p	A	P	a	p	A	P	a	p	A	P
02	b	q	B	Q	b	q	B	Q	b	q	B	Q
03	c	r	C	R	c	r	C	R	c	r	C	R
04	d	s	D	S	d	s	D	S	d	s	D	S
05	e	t	E	T	e	t	E	T	e	t	E	T
06	f	u	F	U	f	u	F	U	f	u	F	U
07	g	v	G	V	g	v	G	V	g	v	G	V
08	h	x	H	X	h	x	H	X	h	x	H	X
09	j	y	J	Y	j	y	J	Y	j	y	J	Y
10	k	z	K	Z	k	z	K	Z	k	z	K	Z
11	l	2	L	4	l	2	L	4	l	2	L	4
12	n	3	N	5	n	3	N	5	n	3	N	5

1) New Marking Layout for SC75, implemented at October 2005.

[illegible]

Technical drawing of a mechanical part with dimensions: 0.4, 0.45, 1.05, 0.4, 0.4.

Pin 1

BCR847BF

Type code

infineon
Manufacturer

Technical drawing of a mechanical part. The main view shows a rectangular part with a width of 8 and a height of 1.16. There are two circular features, each with a diameter of 4. The distance between the centers of these circles is 0.76. A dimension of 0.76 is also shown for the distance from the right edge to the center of the rightmost circular feature. A dimension of 4 is shown for the distance from the left edge to the center of the leftmost circular feature. A dimension of 0.5 is shown for the thickness of the part. A cross-section view is shown on the right, indicating a hatched area. A label 'Pin 1 marking' points to a specific location on the part.

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